### **N-Channel Enhancement-Mode MOS Transistors**

VN10LE VN0605T VN2222LL VN10LM VN0610LL **VN2222LM** 

#### **Product Summary**

Part Number	V <sub>(BR)DSS</sub> Min (V)	$\mathbf{r}_{\mathbf{DS}(\mathbf{on})}\mathbf{Max}(\Omega)$	$V_{GS(th)}(V)$	I <sub>D</sub> Min (A)
VN10LE	60	$5 @ V_{GS} = 10 V$	0.8 to 2.5	0.38
VN10LM		$5 @ V_{GS} = 10 V$	0.8 to 2.5	0.32
VN0605T		$5 @ V_{GS} = 10 V$	0.8 to 3.0	0.18
VN0610LL		$5 @ V_{GS} = 10 V$	0.8 to 2.5	0.28
VN2222LL		$7.5 @ V_{GS} = 5 V$	0.6 to 2.5	0.23
VN2222LM		$7.5 @ V_{GS} = 5 V$	0.6 to 2.5	0.26

#### **Features**

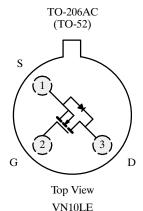
- Low On-Resistance: 2.5 Ω
- Low Threshold: <2.1 V
- Fast Switching Speed: 7 ns
- Low Input and Output Leakage

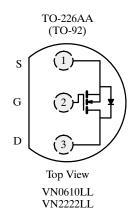
### **Benefits**

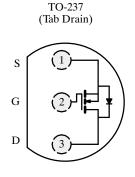
- Low Offset Voltage
- Low-Voltage Operation
- Low Input Capacitance: 22 pF Easily Driven Without Buffering
  - High-Speed Circuits
  - Low Error Voltage

#### **Applications**

- Direct Logic-Level Interface: TTL/CMOS
- Solid State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems

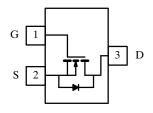






Top View VN10LM VN2222LM

> TO-236 (SOT-23)



Top View VN0605T (V2)\* \*Marking Code for TO-236

## Absolute Maximum Ratings ( $T_A = 25^{\circ}C$ Unless Otherwise Noted)

Parameter		Symbol	VN10LEb	VN10LM	VN0605T	VN0610LL	VN2222LL	VN2222LM	Unit	
Drain-Source Voltage		$V_{DS}$	60	60	60	60	60	60	v	
Gate-Source Voltage		$V_{GS}$	± 20	±30	±30	±30	±30	±30	ľ	
Continuous Drain Current	$T_A = 25$ °C	т	0.38	0.32	0.18	0.28	0.23	0.26		
$(T_{\rm J} = 150^{\circ}{\rm C})$ $T_{\rm A} = 100^{\circ}{\rm C}$		$I_{D}$	0.24	0.2	0.11	0.17	0.14	0.16	A	
Pulsed Drain Current <sup>a</sup>		$I_{DM}$	1.0	1.4	0.72	1.3	1.0	1.0	1	
Power Dissipation	$T_A = 25$ °C	P <sub>D</sub>	1.5	1.0	0.36	0.8	0.8	1.0	w	
	$T_{A} = 100^{\circ} C$		0.6	0.4	0.14	0.32	0.32	0.4	VV	
Maximum Junction-to-Ambient		R <sub>thJA</sub>	400	125	350	156	156	125	°C/ W	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150						°C	

- a. Pulse width limited by maximum junction temperature.b. Reference case for all temperature testing.

### **Specifications**<sup>a</sup>

					Limits						
				VN10LE VN10LM VN0610LL		VN0605T		VN2222LL VN2222LM			
Parameter	Symbol	<b>Test Conditions</b>	Typb	Min	Max	Min	Max	Min	Max	Unit	
Static			_								
Drain-Source	V	$V_{GS} = 0 \text{ V}, I_D = 100 \mu\text{A}$		60				60			
Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_{D} = 10 \mu$	ıA 70			60				v	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 1$ n	nA 2.1	0.8	2.5	0.8	3.0	0.6	2.5		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 2$	0 V		±100 e		±10 0		±10 0		
		$T_{\mathbf{J}}$ :	=125°C				±50 0			nA	
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 3$	0 V		± 100						
Zero Gate-Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 50 \text{ V}, V_{GS} = 0$	V		10		1.0				
		$T_{J}$ =	= 125°C		500		500			μA	
		$V_{DS} = 48 \text{ V}, V_{GS} = 0$	V						10	] μπ	
		$T_{J}$ =	= 125°C						500		
On-State Drain Current <sup>c</sup>	I <sub>D(on)</sub>	$V_{DS} = 10 \ V, V_{GS} = 1$	0 V 1000	750		500		750		mA	
Drain-Source On-Resistance <sup>c</sup>	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 50 \text{ m}$	mA 4.5				7.5				
		$V_{GS} = 5 \text{ V}, I_D = 0.2$	A 4.5		7.5				7.5	Ω	
		$V_{GS} = 10 \text{ V}, I_D = 0.5$	A 2.4		5		5		7.5		
		$T_{J}$ =	= 125°C 4.4		9		10		13.5		
Forward Transconductance <sup>c</sup>	<b>g</b> fs	$V_{DS} = 10 \text{ V}, I_{D} = 0.5$	A 230	100				100		mS	
		$V_{DS} = 10 \text{ V}, I_D = 0.2$	2 A 180			80				1113	
Common Source Output Conductance <sup>c</sup>	gos	$V_{DS} = 5 \text{ V}, I_D = 50 \text{ n}$	nA 500							μs	

# VN10/0605/0610/2222 Series

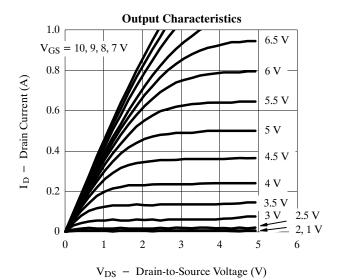
### **Specifications**<sup>a</sup>

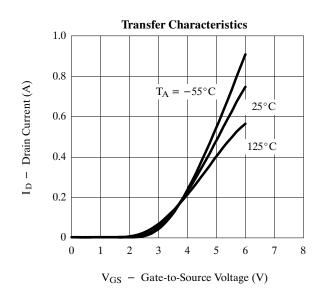
				Limits						
				VN10LE VN10LM VN0610LL		VN0605T		VN2222LL VN2222LM		
Parameter	Symbol	Test Conditions	Typb	Min	Max	Min	Max	Min	Max	Unit
Dynamic	•						-			
Input Capacitance	C <sub>iss</sub>		22		60		60		60	
Output Capacitance	Coss	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}$	11		25		25		25	рF
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1  MHz	2		5		5		5	P
Switching <sup>d</sup>										
Turn-On Time	t <sub>ON</sub>	$V_{DD} = 15 \text{ V}, R_L = 23 \Omega, I_D \approx 0.6 \text{ A}$	7		10				10	
Turn-Off Time	t <sub>OFF</sub>	$V_{GEN} = 10 \text{ V}, R_G = 25 \Omega$	7		10				10	
Turn-On Time	t <sub>ON</sub>	$V_{DD} = 30 \text{ V}, R_{L} = 150 \Omega$ $I_{D} \approx 0.2 \text{ A}$	7				20			ns
Turn-Off Time	t <sub>OFF</sub>	$V_{GEN} = 10 \text{ V}, R_G = 25 \Omega$	11				20			

VNBF06

- $T_A = 25$  °C unless otherwise noted. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- Pulse test: PW  $\leq 300 \,\mu s \,duty \,cycle \,\leq 3\%$ .
- Switching time is essentially independent of operating temperature.
- VN10LE only.

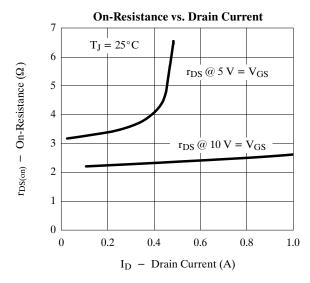
## **Typical Characteristics (25°C Unless Otherwise Noted)**

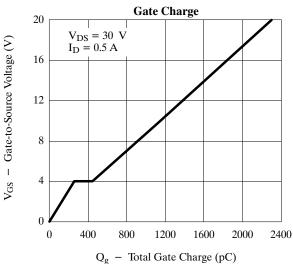


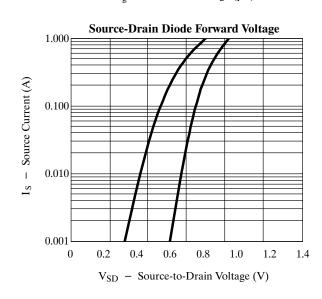


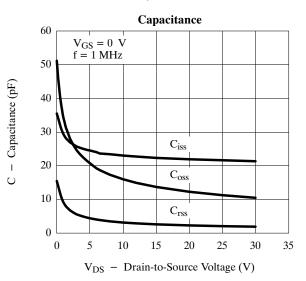
P-37993—Rev. C (08/08/94) 3

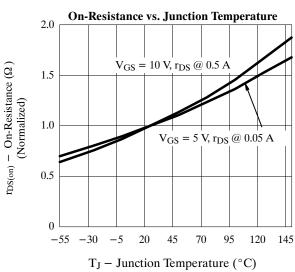
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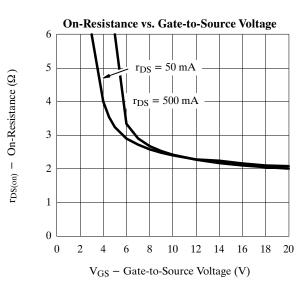




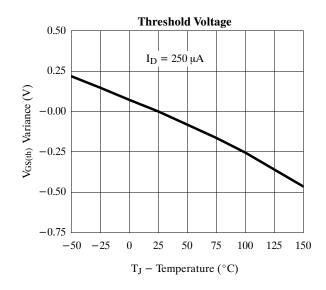


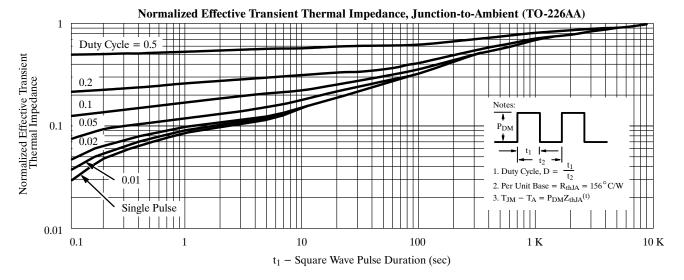






## **Typical Characteristics (25°C Unless Otherwise Noted)**





P-37993—Rev. C (08/08/94)